

	$\tau_Y$ (80°C)	$\tau_Y$ (20°C)
Standard silicon	90 min	1.3 y
SINTEF	220 min	3.2 y
CiS	350 min	5 y
STMicroelectronics	450 min	6.5 y

Table 1.: Reverse annealing time constants  $\tau_Y$  as measured at 80°C for standard and oxygenated silicon produced by three different manufacturers. The activation energy given in Ref. [9] has been used to scale the time constant to 20°C.

	Standard Silicon		Oxygen-enriched Silicon	
	Neutrons	Protons	Neutrons	Protons
$g_a$	$1.8 \times 10^{-2} \text{ cm}^{-1}$	-	$1.4 \times 10^{-2} \text{ cm}^{-1}$	-
$\tau_a(20^\circ\text{C})$	55 h	-	70 h	-
$g_c$	$1.5 \times 10^{-2} \text{ cm}^{-1}$	$1.9 \times 10^{-2} \text{ cm}^{-1}$	$2.0 \times 10^{-2} \text{ cm}^{-1}$	$5.3 \times 10^{-3} \text{ cm}^{-1}$
$N_{C0}/N_{\text{eff}0}$	0.70	-	0.45	1.0
$g_Y$	$5.2 \times 10^{-2} \text{ cm}^{-1}$	$6.6 \times 10^{-2} \text{ cm}^{-1}$	$4.8 \times 10^{-2} \text{ cm}^{-1}$	$2.3 \times 10^{-2} \text{ cm}^{-1}$ (*)
$\tau_Y(20^\circ\text{C})$	480 d	-	800 d	950 d

(\*) saturation value measured for  $\Phi_{\text{eq}} = 6 \cdot 10^{14} \text{ cm}^{-2}$

Table 2.: Damage parameters for standard and oxygen enriched silicon as given in Ref.[3] and used for the damage projections shown in Fig. 14. The new data given in Table 1 have not been considered yet.